

**IN THE SPECIFICATION**

Paragraph at page 16, line 3:

The cross sectional structure of the integrated LED/driving-IC chip 200 of the second embodiment will next be described. As shown in FIG. 9, the integrated LED/driving-IC chip 200 has a structure of an Si substrate 101, a first interdielectric layer 103, an adhesion layer 104 made of material such as polycrystalline silicon or amorphous silicon, an electrically conductive layer 105, an LED epitaxial film 206, a second interdielectric layer 209, and an individual interconnecting layer 207, which are formed in this order. As shown in FIG. 9, the LED epitaxial film 206 has a structure of an n-type GaAs layer 211, an n-type  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  layer 212 ( $0 \leq x \leq 1$ ), an n-type  $\text{Al}_y\text{Ga}_{1-y}\text{As}$  layer 213 ( $0 \leq y \leq 1$ ), an n-type  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  layer [[214s]] 214 ( $0 \leq z \leq 1$ ), and a GaAs layer 215, which are grown in this order. A Zn diffusion region 216 is formed in the n-type  $\text{Al}_y\text{Ga}_{1-y}\text{As}$  layer 213 and n-type  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  layer 214 under the GaAs layer 215. The GaAs layer 215 and Zn diffusion region 216 are of the p-type.